Silicon NPN Power Transistors 2SC4278

DESCRIPTION

·With TO-247 package
·Complement to type 2SA1633
·High current and high power capability

APPLICATIONS

·For audio output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

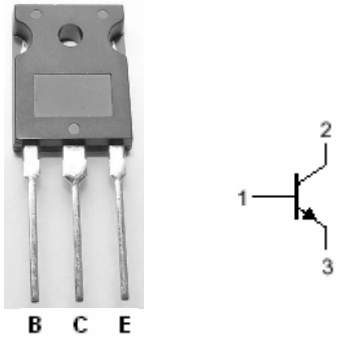

Fig.1 simplified outline (TO-247) and symbol

Absolute maximum ratings(Tc=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	150	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current (DC)		10	A
P_D	Total power dissipation	T_C=25□	100	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=25mA; I_B=0	150			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=5A ;I_B=0.5A			1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=5A ;I_B=0.5A			2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=150V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=1A ; V_{CE}=5V	60		320	
f_T	Transition frequency	I_C=1A ; V_{CE}=10V		20		MHz

◆ **h_{FE} Classifications**

D	E	F
60-120	100-200	160-320

PACKAGE OUTLINE

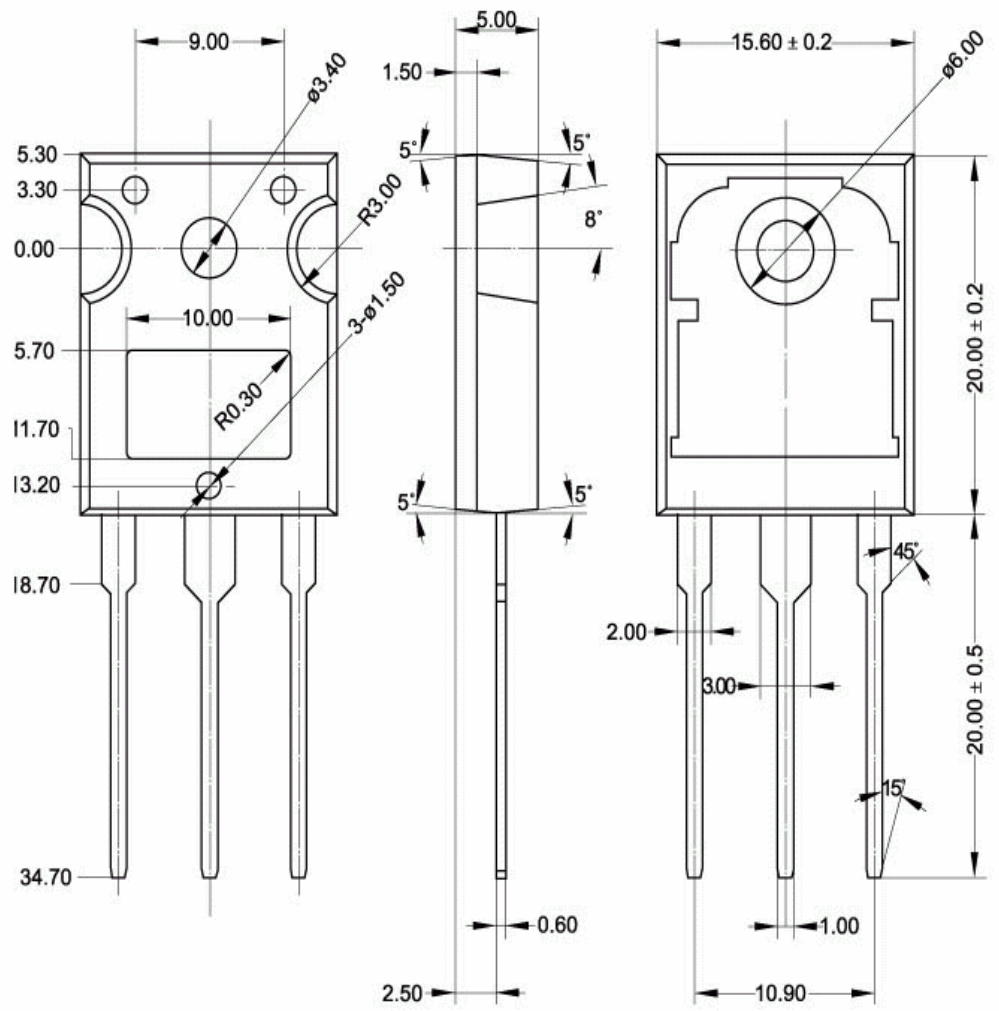

Fig.2 Outline dimensions